

ABSTRACT

A semiconductor device having an interlayer insulation film with a low capacitance and a method of fabricating the same are disclosed. An example semiconductor device having a multi-layered metal wire structure includes first and second interlayer insulation films provided between lower metal wire layers and upper metal wire layers. The example semiconductor device also includes air gaps formed in the first interlayer insulation film at an interlevel between the upper and lower metal wire layers and via holes connecting the upper and lower metal wire layers.